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FDS8984 N-Channel PowerTrench[®] MOSFET

30V, 7A, 23m Ω

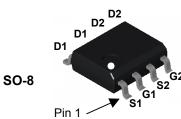
General Description

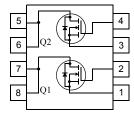
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $r_{\text{DS}(\text{ON})}$ and fast switching speed.

Features

- Max $r_{DS(on)}$ = 23mΩ, V_{GS} = 10V, I_D = 7A
- Max $r_{DS(on)}$ = 30mΩ, V_{GS} = 4.5V, I_D = 6A
- Low gate charge
- 100% R_G tested
- RoHS Compliant







MOSFET Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DS}	Drain to Source Voltage		30	V
V _{GS}	Gate to Source Voltage		±20	V
I _D	Drain Current Continuous	(Note 1a)	7	А
	Pulsed		30	А
E _{AS}	Single Pulse Avalache Energy	(Note 2)	32	mJ
D	Power Dissipation for Single Operation		1.6	W
P _D	Derate above 25°C		13	mW/°C
T _J , T _{STG}	Operating and Storage Temperature		-55 to 150	°C
Therma R _{θJA}	Characteristics	(Note 1a)	78	°C/W
	,	()	-	-
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	40	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDS8984	FDS8984	SO-8	330mm	12mm	2500 units

FDS8984 N-Channel PowerTrench[®] MOSFET

May 2007

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units	
Off Chara	acteristics						
BV _{DSS}	Drain to Source Breakdown Voltage	I _D = 250μA, V _{GS} = 0V	30			V	
ΔBV _{DSS} ΔTJ	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu A$, referenced to $25^{\circ}C$		23		mV/°C	
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24V$ $V_{GS} = 0V$ $T_{J} = 125^{\circ}C$			1 250	μA	
I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20 V, V_{DS} = 0 V$			±100	nA	
On Chara	cteristics (Note 3)						
	Gate to Source Threshold Voltage	1/-1/-250.0	1.2	1.7	2.5	V	
V _{GS(th)}	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$ $I_D = 250\mu A$, referenced to	1.2	1.7	2.5		
$\frac{\Delta V_{GS(th)}}{\Delta T_{.l}}$	Temperature Coefficient	1 _D = 250μA, telefenced to 25°C		- 4.3		mV/°C	
		V _{GS} = 10V, I _D = 7A		19	23		
	Drain to Course On Desistance	$V_{GS} = 4.5V, I_D = 6A$		24	30		
DS(on)	Drain to Source On Resistance	$V_{GS} = 10V, I_D = 7A,$ T _J = 125°C		26	32	mΩ	
C _{iss}	Characteristics Input Capacitance			475	635	pF	
C _{oss}	Output Capacitance	f = 1.0 MHz		100	135	pF	
C _{rss}	Reverse Transfer Capacitance			65	100	pF	
C _{rss}	Gate Resistance	f = 1MHz		65 0.9	100 1.6	p⊦ Ω	
C _{rss} R _G		f = 1MHz				· ·	
C _{rss} R _G Switching	Gate Resistance	f = 1MHz				<u> </u>	
C _{rss} R _G Switching t _{d(on)}	Gate Resistance g Characteristics (Note 3)			0.9	1.6	Ω	
C _{rss} R _G Switchin(d(on)	Gate Resistance g Characteristics (Note 3) Turn-On Delay Time	f = 1MHz V _{DD} = 15V, I _D = 7A V _{GS} = 10V, R _{GS} = 33Ω		0.9 5	1.6	Ω ns	
C _{rss} R _G Switching d(on) r d(off)	Gate Resistance	V _{DD} = 15V, I _D = 7A		0.9 5 9	1.6 10 18	Ω ns ns	
C _{rss} R _G Switching t _{d(on)} t _r t _{d(off)} t _f	Gate Resistance Characteristics (Note 3) Turn-On Delay Time Rise Time Turn-Off Delay Time	$V_{DD} = 15V, I_D = 7A$ $V_{GS} = 10V, R_{GS} = 33\Omega$ $V_{DS} = 15V, V_{GS} = 10V,$		0.9 5 9 42	1.6 10 18 68	Ω ns ns ns	
C _{rss} R _G Switching t _{d(on)} t _r t _{d(off)} t _f Q _g	Gate Resistance Characteristics (Note 3) Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time	$V_{DD} = 15V, I_{D} = 7A$ $V_{GS} = 10V, R_{GS} = 33\Omega$ $V_{DS} = 15V, V_{GS} = 10V,$ $I_{D} = 7A$		0.9 5 9 42 21	1.6 10 18 68 34	ns ns ns ns	
C _{rss} R _G Switching i ^t d(on) i ^t r i ^t d(off) i ^t f Q _g Q _g	Gate Resistance Characteristics (Note 3) Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Total Gate Charge	$V_{DD} = 15V, I_D = 7A$ $V_{GS} = 10V, R_{GS} = 33\Omega$ $V_{DS} = 15V, V_{GS} = 10V,$		0.9 5 9 42 21 9.2	1.6 10 18 68 34 13	Ω ns ns ns ns ns	
C _{rss} R _G Switchin (t _{d(on)} t _r t _{d(off)} t _f Q _g Q _{gs}	Gate Resistance Characteristics (Note 3) Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Total Gate Charge Total Gate Charge	$V_{DD} = 15V, I_D = 7A$ $V_{GS} = 10V, R_{GS} = 33\Omega$ $V_{DS} = 15V, V_{GS} = 10V,$ $I_D = 7A$ $V_{DS} = 15V, V_{GS} = 5V,$		0.9 5 9 42 21 9.2 5.0	1.6 10 18 68 34 13	Ω ns ns ns ns ns nc	
$\begin{array}{c} C_{rss} \\ \hline R_{G} \\ \hline \\ \textbf{Switching} \\ \hline \\ \textbf{Switching} \\ \hline \\ t_{d(on)} \\ t_{r} \\ \hline \\ t_{d(off)} \\ \hline \\ t_{f} \\ \hline \\ Q_{g} \\ \hline \\ Q_{g} \\ \hline \\ Q_{g} \\ \hline \\ Q_{gg} \\ \hline \\ \\ Q_{gg} \\ \hline \hline \\ Q_{gg} \\ \hline \hline \\ Q_{gg} \\ \hline \hline \\ Q_{gg} \hline \hline \\ Q_{gg} \hline \hline \\ Q_{gg} \\ \hline \hline \\ Q_{gg} \hline \hline \\ Q_{gg} \\ \hline \hline \\ Q_{gg} \hline \hline \hline \\ \hline \hline \hline \hline \hline \\ Q_{gg} \hline \hline \hline \\ \hline \hline \hline \hline \hline \hline \hline \\ \hline \hline \hline \hline \hline \hline \hline $	Gate Resistance Characteristics (Note 3) Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Total Gate Charge Gate to Source Gate Charge Gate to Drain "Miller" Charge	$V_{DD} = 15V, I_D = 7A$ $V_{GS} = 10V, R_{GS} = 33\Omega$ $V_{DS} = 15V, V_{GS} = 10V,$ $I_D = 7A$ $V_{DS} = 15V, V_{GS} = 5V,$		0.9 5 9 42 21 9.2 5.0 1.5	1.6 10 18 68 34 13	Ω ns ns ns ns nc nC	
$\begin{array}{c} C_{rss} \\ \hline R_G \\ \hline \textbf{Switching} \\ \hline \textbf{Switching} \\ \hline \textbf{Switching} \\ \hline \textbf{t}_{d(on)} \\ \hline \textbf{t}_r \\ \hline \textbf{t}_{d(off)} \\ \hline \textbf{t}_f \\ \hline \textbf{Q}_g \\ \hline \textbf{Q}_g \\ \hline \textbf{Q}_{gd} \\ \hline \textbf{Q}_{gd} \\ \hline \textbf{Drain-Sol} \end{array}$	Gate Resistance g Characteristics (Note 3) Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Total Gate Charge Gate to Source Gate Charge Gate to Drain "Miller" Charge urce Diode Characteristics	$V_{DD} = 15V, I_{D} = 7A$ $V_{GS} = 10V, R_{GS} = 33\Omega$ $V_{DS} = 15V, V_{GS} = 10V,$ $I_{D} = 7A$ $V_{DS} = 15V, V_{GS} = 5V,$ $I_{D} = 7A$		0.9 5 9 42 21 9.2 5.0 1.5	1.6 10 18 68 34 13	Ω ns ns ns ns nc nC	
C_{rss} R_{G} Switching $\frac{k_{d(on)}}{k_{r}}$ $\frac{k_{d(off)}}{k_{f}}$ Q_{g} Q_{gs} Q_{gd} Drain-So	Gate Resistance Characteristics (Note 3) Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Total Gate Charge Gate to Source Gate Charge Gate to Drain "Miller" Charge	$V_{DD} = 15V, I_D = 7A$ $V_{GS} = 10V, R_{GS} = 33\Omega$ $V_{DS} = 15V, V_{GS} = 10V,$ $I_D = 7A$ $V_{DS} = 15V, V_{GS} = 5V,$		0.9 5 9 42 21 9.2 5.0 1.5 2.0	1.6 10 18 68 34 13 7	Ω ns ns ns ns nc nC nC nC	
C _{rss} R _G Switching t _{d(on)} t _r t _{d(off)} t _f Q _g Q _g Q _{gs} Q _{gd}	Gate Resistance g Characteristics (Note 3) Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Total Gate Charge Gate to Source Gate Charge Gate to Drain "Miller" Charge urce Diode Characteristics	$V_{DD} = 15V, I_{D} = 7A$ $V_{GS} = 10V, R_{GS} = 33\Omega$ $V_{DS} = 15V, V_{GS} = 10V,$ $I_{D} = 7A$ $V_{DS} = 15V, V_{GS} = 5V,$ $I_{D} = 7A$ $I_{SD} = 7A$		0.9 5 9 42 21 9.2 5.0 1.5 2.0 0.9	1.6 10 18 68 34 13 7 1.25	Ω ns ns ns ns nc nC nC V	

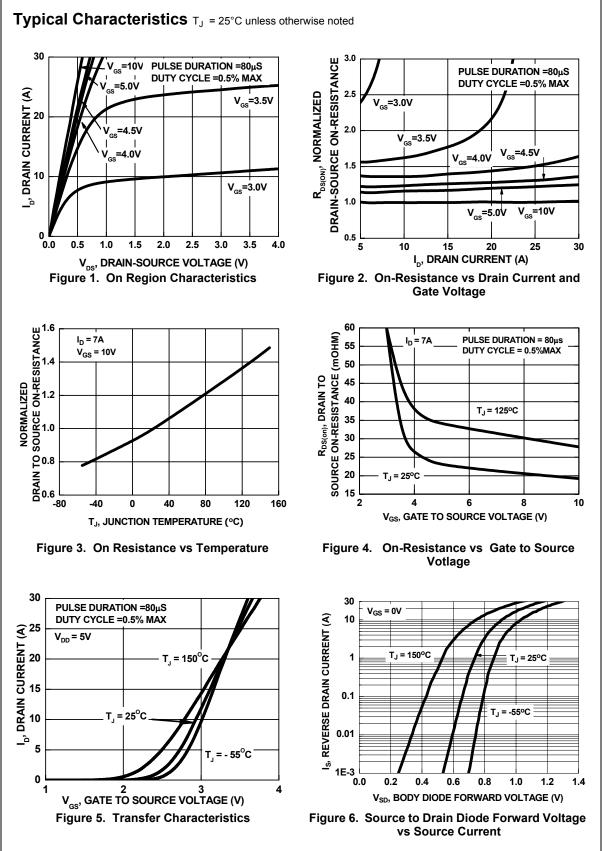


mounted on a 0.02 in pad of oz copper 0000

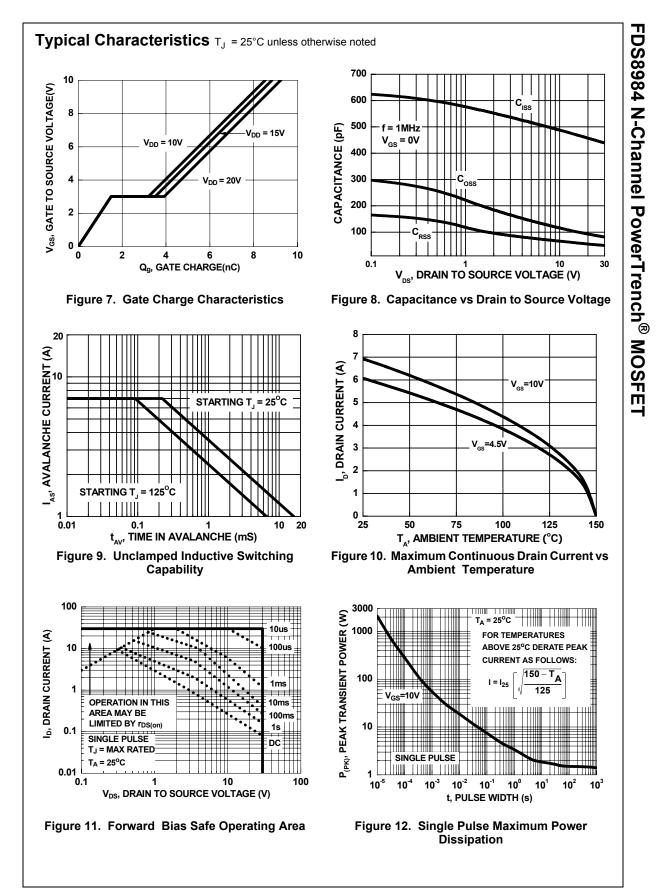
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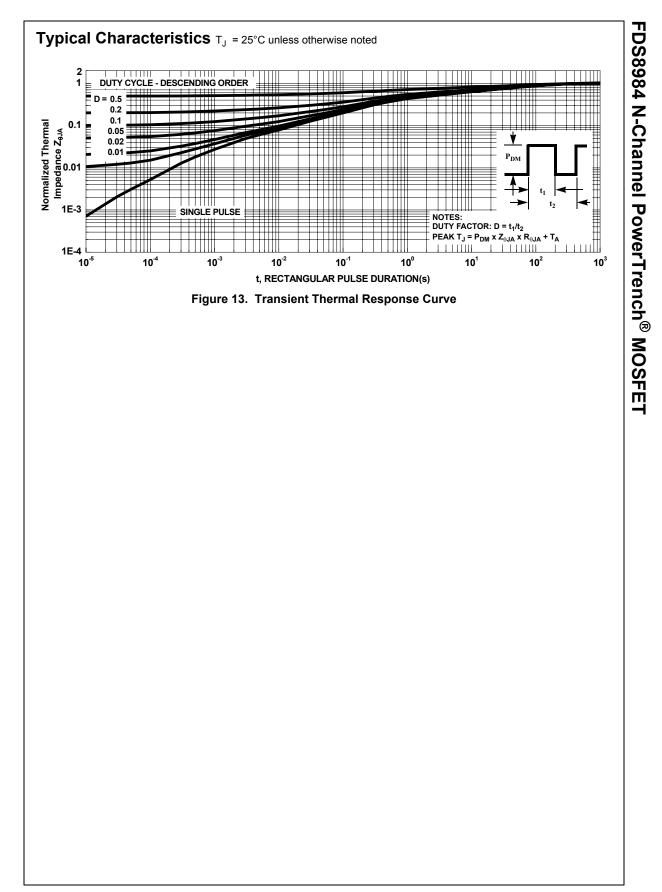
Scale 1 : 1 on letter size paper

2: Starting  $T_J$  = 25°C, L = 1mH,  $I_{AS}$  = 8A,  $V_{DD}$  = 27V,  $V_{GS}$  = 10V. 3: Pulse Test:Pulse Width <300 $\mu$ S, Duty Cycle <2%.









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TinyBoost™

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